

DATA SHEET

BFR30; BFR31

N-channel field-effect transistors

Product specification
Supersedes data of April 1991

1997 Dec 05



N-channel field-effect transistors

BFR30; BFR31

DESCRIPTION

Planar epitaxial symmetrical junction N-channel field-effect transistor in a plastic SOT23 package.

APPLICATIONS

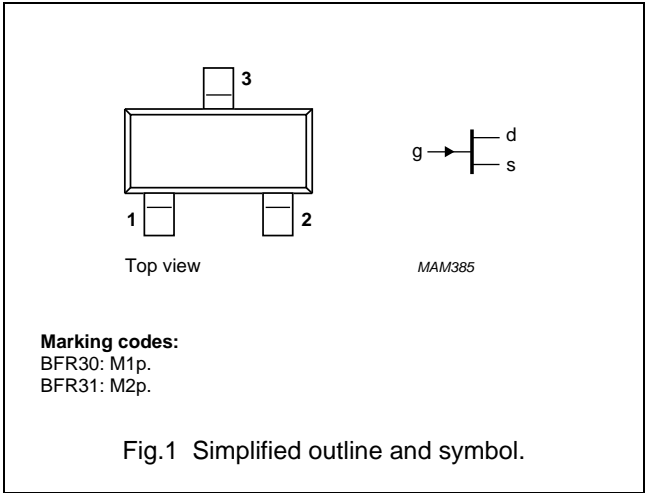
- Low level general purpose amplifiers in thick and thin-film circuits.

PINNING - SOT23

PIN	SYMBOL	DESCRIPTION
1	d	drain ⁽¹⁾
2	s	source ⁽¹⁾
3	g	gate

Note

1. Drain and source are interchangeable.



CAUTION

This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		–	± 25	V
V_{GSO}	gate-source voltage	open drain	–	–25	V
P_{tot}	total power dissipation	$T_{amb} \leq 40\text{ }^{\circ}\text{C}$	–	250	mW
I_{DSS}	drain current BFR30 BFR31	$V_{GS} = 0$; $V_{DS} = 10\text{ V}$	4 1	10 5	mA mA
$ y_{fs} $	common-source transfer admittance BFR30 BFR31	$I_D = 1\text{ mA}$; $V_{DS} = 10\text{ V}$; $f = 1\text{ kHz}$	1 1.5	4 4.5	mS mS

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{DS}	drain-source voltage		–	±25	V
V _{DGO}	drain-gate voltage	open source	–	–25	V
V _{GSO}	gate-source voltage	open drain	–	–25	V
I _D	drain current		–	10	mA
I _G	forward gate current (DC)		–	5	mA
P _{tot}	total power dissipation	T _{amb} ≤ 40 °C; note 1; see Fig.2	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	operating junction temperature		–	150	°C

Note

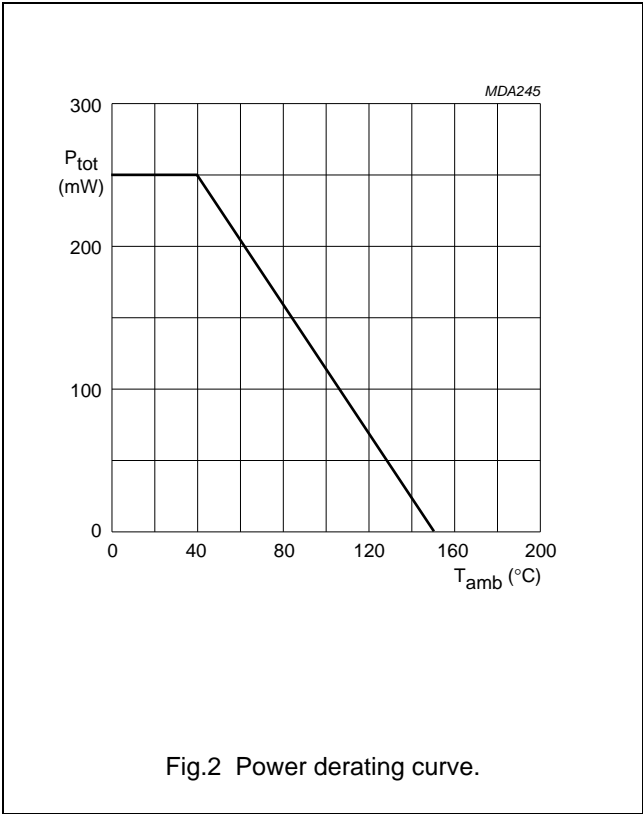
1. Mounted on a ceramic substrate of 8 × 10 × 0.7 mm.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	430	K/W

Note

1. Mounted on a ceramic substrate of 8 × 10 × 0.7 mm.



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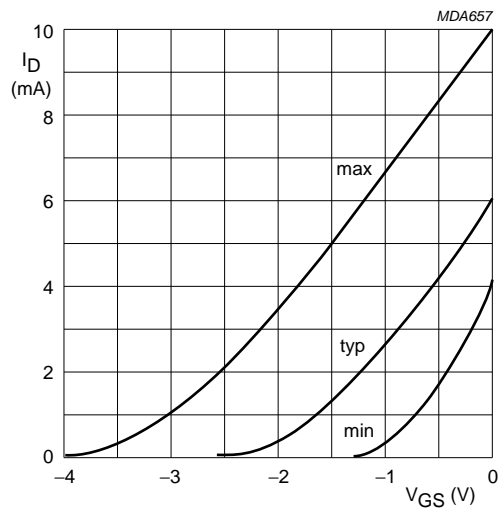
CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{GSS}	gate cut-off current	$V_{DS} = 0; V_{GS} = -10\text{ V}$	—	−0.2	nA
I_{DSS}	drain current BFR30 BFR31	$V_{GS} = 0; V_{DS} = 10\text{ V}$	4 1	10 5	mA mA
V_{GS}	gate-source voltage BFR30 BFR31	$I_D = 1\text{ mA}; V_{DS} = 10\text{ V}$	−0.7 0	−3 −1.3	V V
V_{GS}	gate-source voltage BFR30 BFR31	$I_D = 50\text{ }\mu\text{A}; V_{DS} = 10\text{ V}$	— —	−4 −2	V V
V_{GSoff}	gate-source cut-off voltage BFR30 BFR31	$I_D = 0.5\text{ nA}; V_{DS} = 10\text{ V}$	— —	−5 −2.5	V V
$ y_{fs} $	common-source transfer admittance BFR30 BFR31	$I_D = 1\text{ mA}; V_{DS} = 10\text{ V}; f = 1\text{ kHz};$ $T_{amb} = 25\text{ °C}$	1 1.5	4 4.5	mS mS
$ y_{fs} $	common-source transfer admittance BFR30 BFR31	$I_D = 200\text{ }\mu\text{A}; V_{DS} = 10\text{ V}; f = 1\text{ kHz};$ $T_{amb} = 25\text{ °C}$	0.5 0.75	— —	mS mS
$ y_{os} $	common source output admittance BFR30 BFR31	$I_D = 1\text{ mA}; V_{DS} = 10\text{ V}; f = 1\text{ kHz}$	— —	40 25	μS μS
$ y_{os} $	common source output admittance BFR30 BFR31	$I_D = 200\text{ }\mu\text{A}; V_{DS} = 10\text{ V}; f = 1\text{ kHz}$	— —	20 15	μS μS
C_{is}	input capacitance	$V_{DS} = 10\text{ V}; f = 1\text{ MHz}$ $I_D = 1\text{ mA}$ $I_D = 0.2\text{ nA}$	— —	4 4	pF pF
C_{rs}	feedback capacitance	$V_{DS} = 10\text{ V}; f = 1\text{ MHz}; T_{amb} = 25\text{ °C}$ $I_D = 1\text{ mA}$ $I_D = 200\text{ }\mu\text{A}$	— —	1.5 1.5	pF pF
V_n	equivalent input noise voltage	$I_D = 200\text{ }\mu\text{A}; V_{DS} = 10\text{ V};$ $B = 0.6\text{ to }100\text{ Hz}$	—	0.5	μV

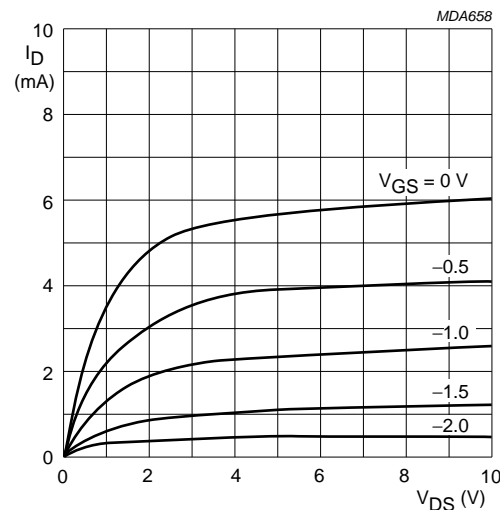
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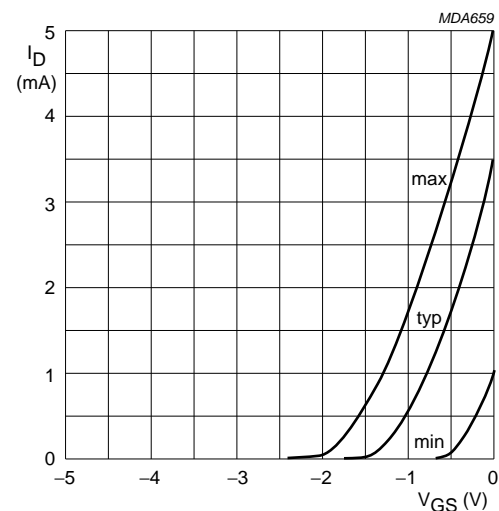
BFR30.
 $V_{DS} = 10\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$.

Fig.3 Input characteristics.



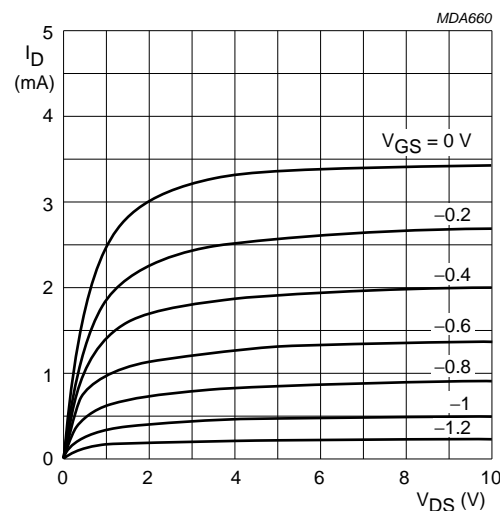
BFR30.
 $T_j = 25\text{ }^\circ\text{C}$.

Fig.4 Output characteristics; typical values.



BFR31.
 $V_{DS} = 10\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$.

Fig.5 Input characteristics.

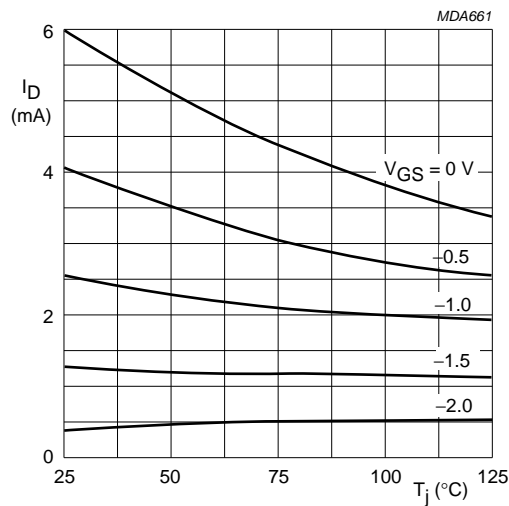


BFR31.
 $T_j = 25\text{ }^\circ\text{C}$.

Fig.6 Output characteristics; typical values.

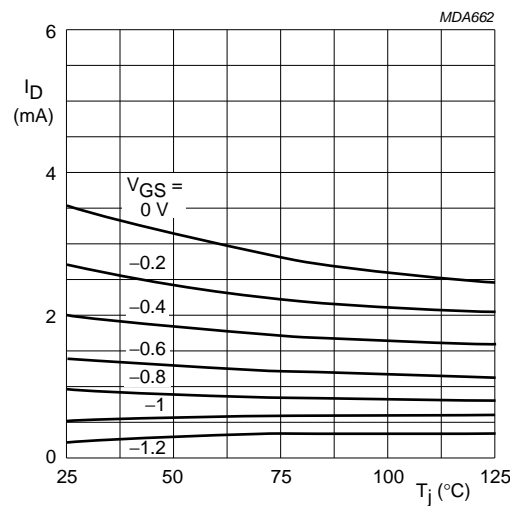
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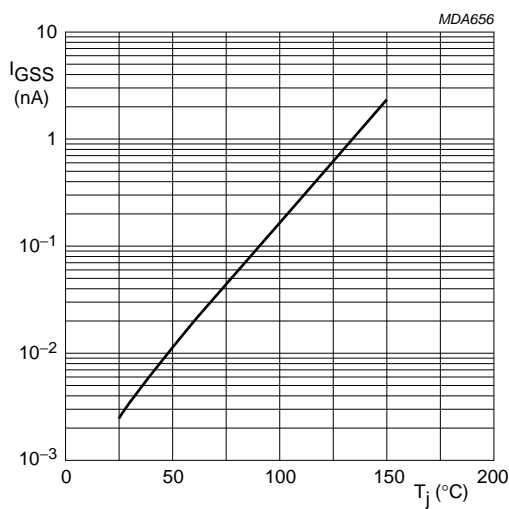
BFR30.
 $V_{DS} = 10\text{ V}.$

Fig.7 Drain current as a function of junction temperature; typical values.



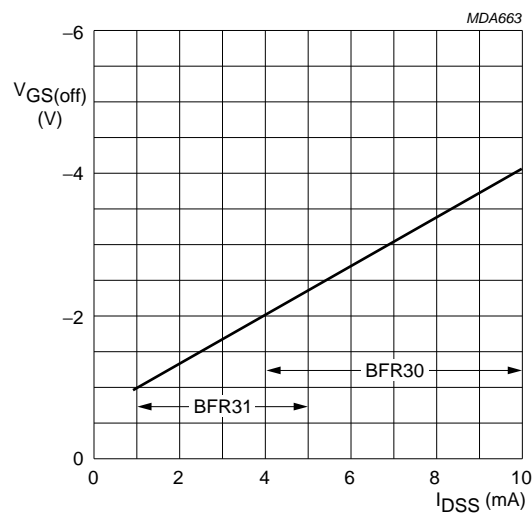
BFR31.
 $V_{DS} = 10\text{ V}.$

Fig.8 Drain current as a function of junction temperature; typical values.



$V_{GS} = -10\text{ V}; V_{DS} = 0.$

Fig.9 Gate cut-off current as a function of junction temperature; typical values.

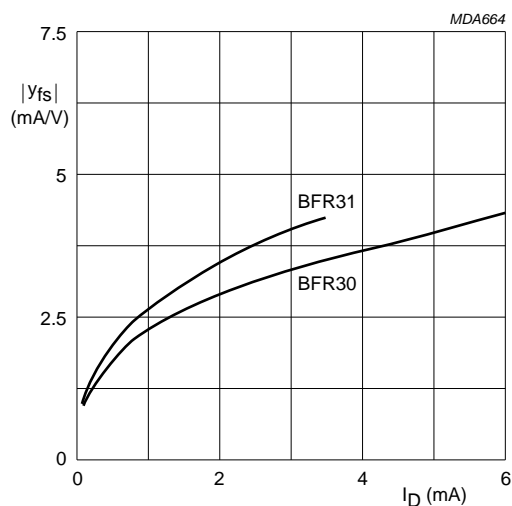


$I_D = 0.5\text{ nA}; V_{DS} = 10\text{ V}; V_{GS} = 0; T_j = 25\text{ °C}.$

Fig.10 Gate-source cut-off voltage as a function of drain current; typical values.

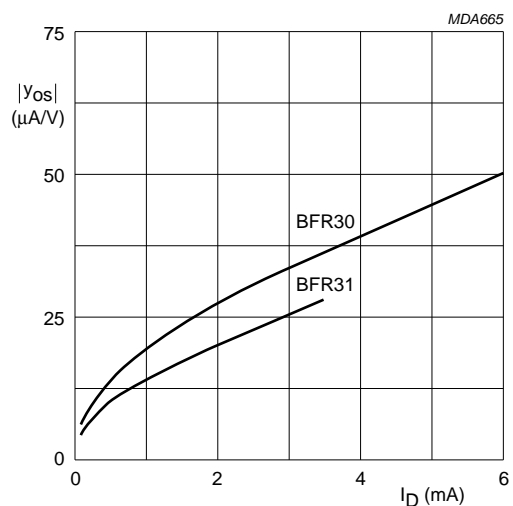
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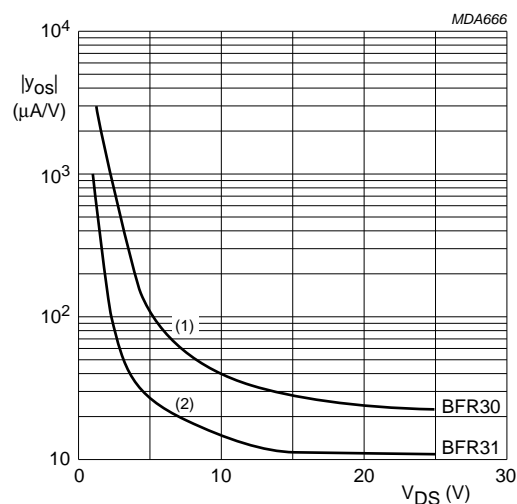
$V_{DS} = 10\text{ V}$; $f = 1\text{ kHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.11 Common source transfer admittance as a function of drain current; typical values.



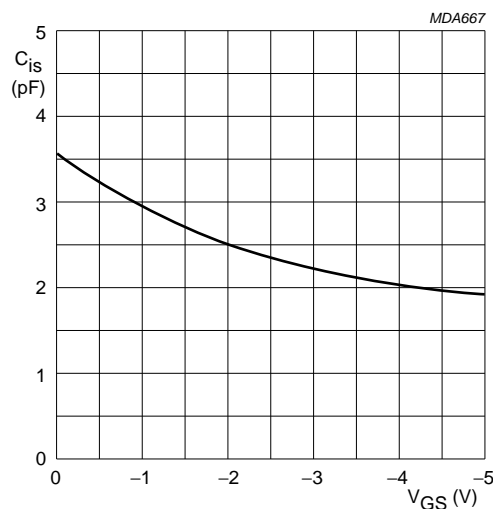
$V_{DS} = 10\text{ V}$; $f = 1\text{ kHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.12 Common source output admittance as a function of drain current; typical values.



$f = 1\text{ kHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.
(1) $I_D = 4\text{ mA}$. (2) $I_D = 1\text{ mA}$.

Fig.13 Common source output admittance as a function of drain-source voltage; typical values.

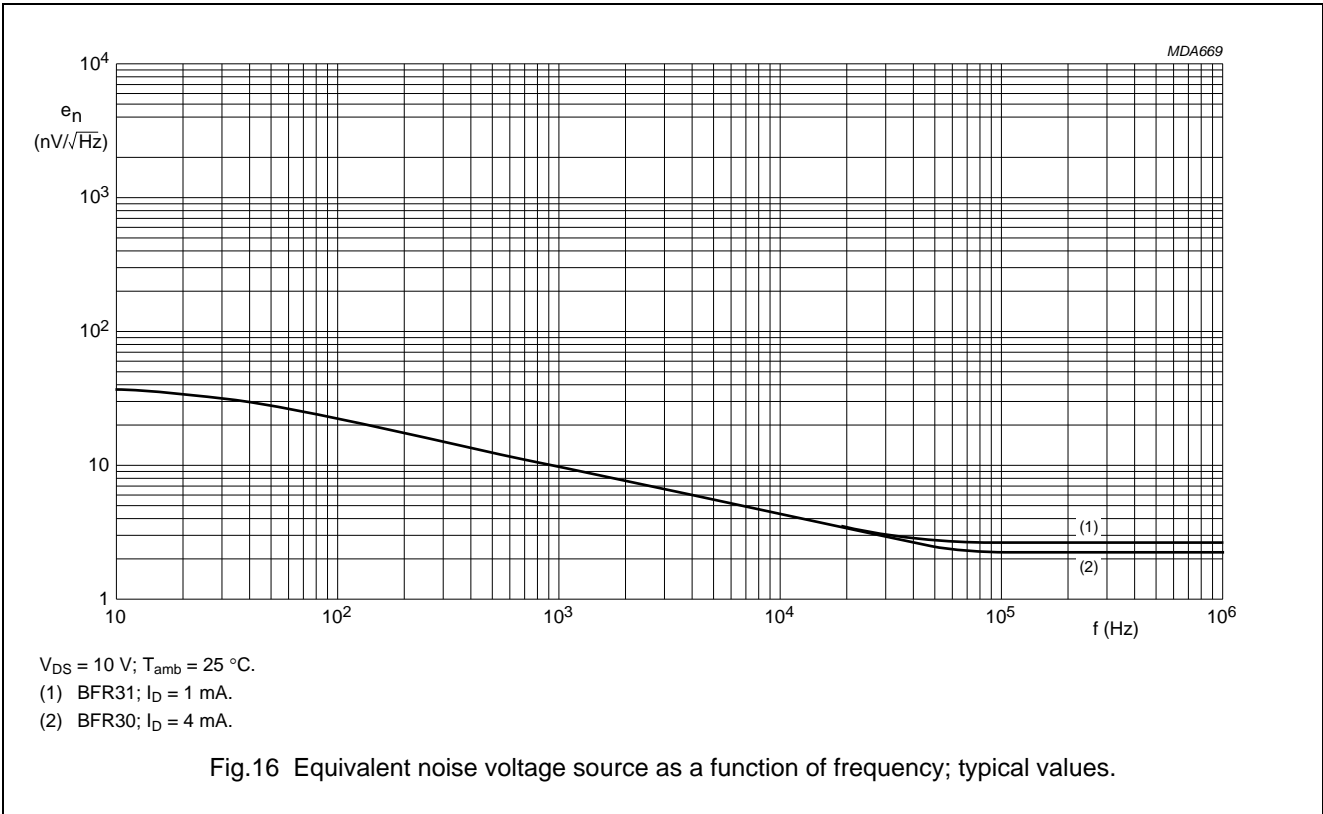
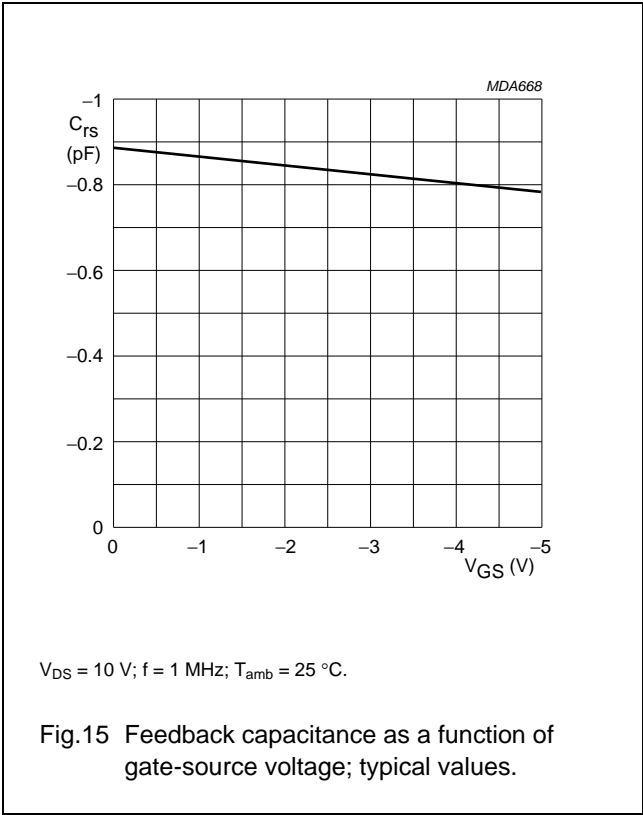


$V_{DS} = 10\text{ V}$; $f = 1\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.14 Input capacitance as a function of gate-source voltage; typical values.

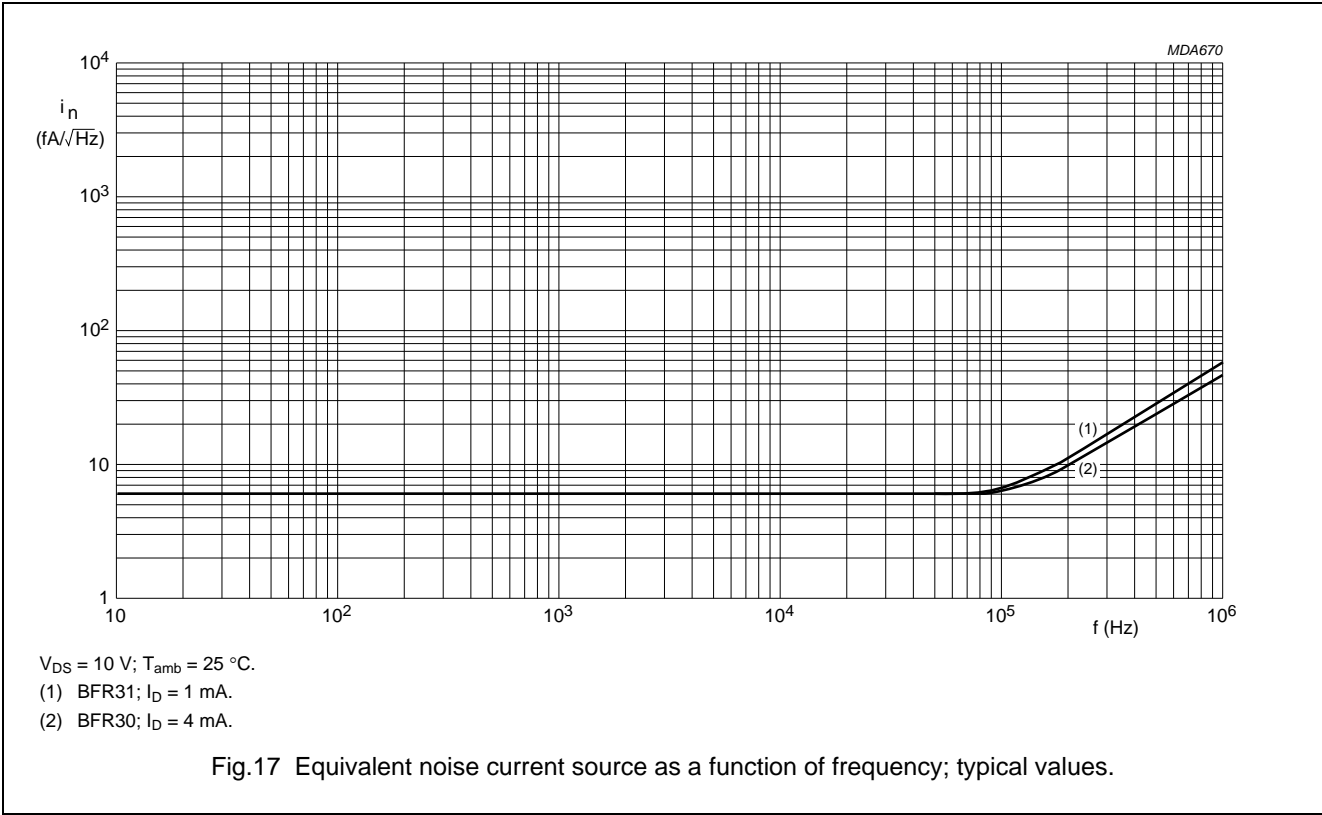
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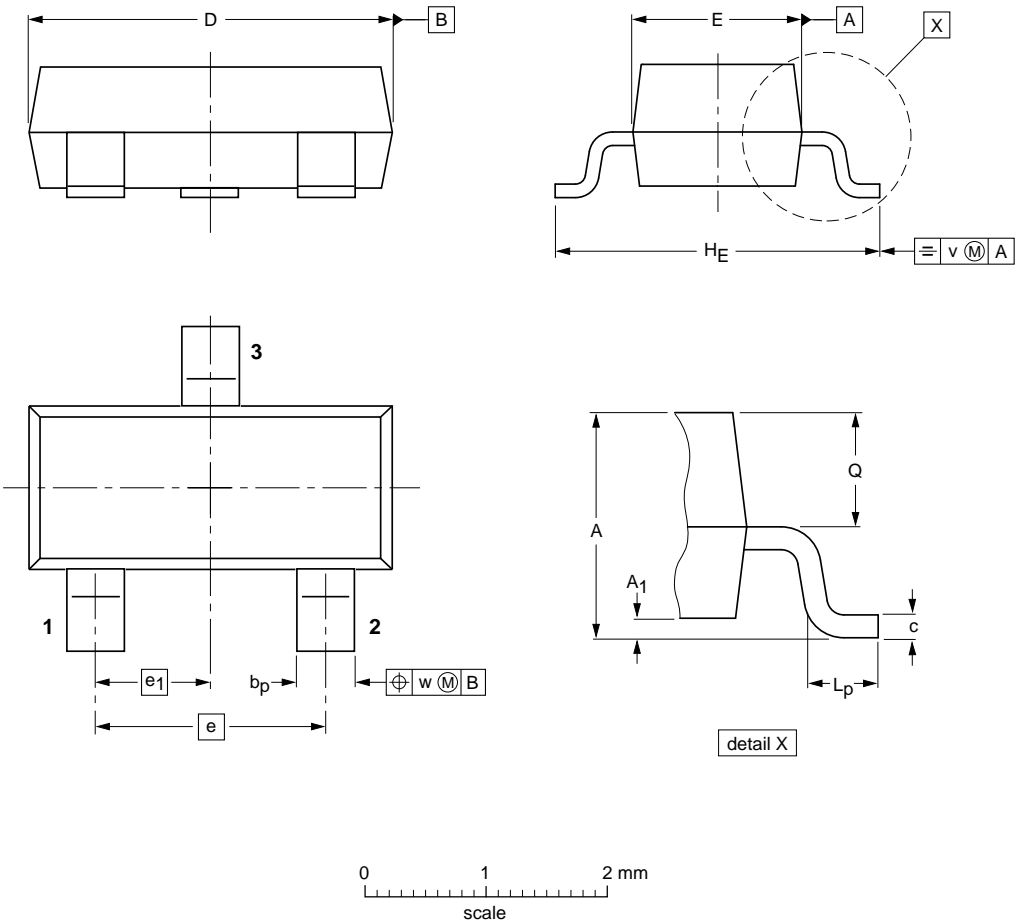
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PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				04-11-04 06-03-16

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
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Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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